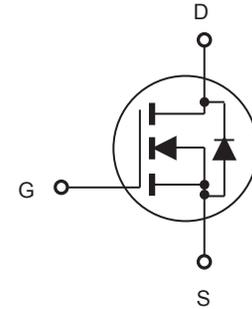


N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- 60V, 100A, $R_{DS(ON)} = 6.2m\Omega$ @ $V_{GS} = 10V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead-free plating ; RoHS compliant.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	100	A
Drain Current-Pulsed ^a	I_{DM}	360	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P_D	100	W
		0.66	W/ $^\circ\text{C}$
Single Pulsed Avalanche Energy ^d	E_{AS}	272	mJ
Single Pulsed Avalanche Current ^d	I_{AS}	33	A
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$